

2SA965-Y(F,M)

2SA965-Y(F,M) Information



Part Number	2SA965-Y(F,M)	
Manufacturer	Toshiba Semiconductor and Storage	
Category	Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single	
Description	TRANS PNP 800MA 120V TO226-3	
Package	TO-226-3, TO-92-3 Long Body	
	For the pricing/inventory/lead time, please contact us Website: https://www.heisener.com E-mail: salesdept@heisener.com	



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For Reference Only

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2SA965-Y(F,M) Specifications

Manufacturer Part Number2SA965-Y(F,M)ManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V@ 50mA, 500mACurrent - Collector Cutoff (Max)800mA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM		
CategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V@ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120VHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageKTM	Manufacturer Part Number	2SA965-Y(F,M)
Transistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, IcIV @ 50mA, 500mACurrent - Collector Cutoff (Max)000nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Manufacturer	Toshiba Semiconductor and Storage
PackageTO-226-3, TO-92-3 Long BodySeries-Transistor TypePNPCurrent - Collector (Lc) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Category	Discrete Semiconductor Products
Series-Stries-Transistor TypePNPCurrent - Collector (Lo) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM		Transistors - Bipolar (BJT) - Single
Transistor TypePNPCurrent - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageKSTM	Package	TO-226-3, TO-92-3 Long Body
Current - Collector (Ic) (Max)800mAVoltage - Collector Emitter Breakdown (Max)120VVcc Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Series	-
Voltage - Collector Emitter Breakdown (Max)120VVce Saturation (Max) @ Ib, Ic1V @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Transistor Type	PNP
Yce Saturation (Max) @ Ib, IcIV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Yce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Current - Collector (Ic) (Max)	800mA
Current - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Voltage - Collector Emitter Breakdown (Max)	120V
DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 100mA, 5VPower - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Vce Saturation (Max) @ Ib, Ic	1V @ 50mA, 500mA
Power - Max900mWFrequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Current - Collector Cutoff (Max)	100nA (ICBO)
Frequency - Transition120MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	DC Current Gain (hFE) (Min) @ Ic, Vce	80 @ 100mA, 5V
Operating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Power - Max	900mW
Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Frequency - Transition	120MHz
Package / CaseTO-226-3, TO-92-3 Long BodySupplier Device PackageLSTM	Operating Temperature	150°C (TJ)
Supplier Device Package LSTM	Mounting Type	Through Hole
	Package / Case	TO-226-3, TO-92-3 Long Body
Report errors ⁶	Supplier Device Package	LSTM
Report crists.		Report errors?

2SA965-Y(F,M) Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

2SA965-Y(F,M) Payment Methods





If you have any question about 2SA965-Y(F,M), please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com